

Pb Free Plating Product

# 10A05 thru 10A10



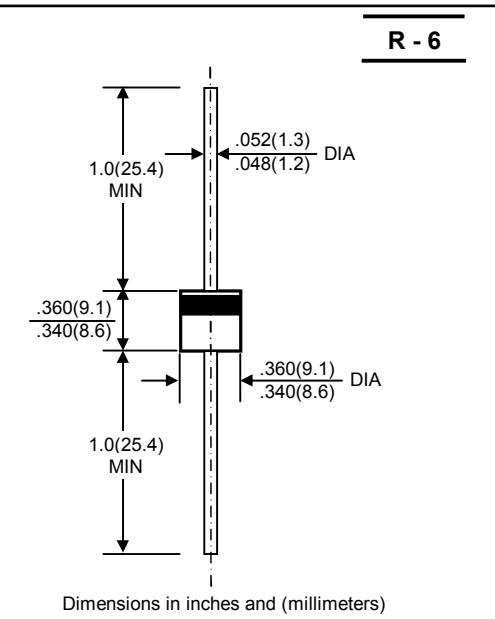
10.0 Ampere Plastic Silicon General Purpose Rectifier Diodes

## Features

- Low cost
- Diffused junction
- Low forward voltage drop
- Low reverse leakage current
- High current capability
- The plastic material carries UL recognition 94V-0

## Mechanical Data

- **Case:** JEDEC R-6 molded plastic
- **Polarity:** Color band denotes cathode
- **Mounting position:** Any



## Absolute Maximum Ratings and Characteristics

Ratings at 25°C ambient temperature unless otherwise specified. Single phase, half wave, 60Hz, resistive or inductive load.. For capacitive load, derate current by 20%.

	Symbols	10A05	10A1	10A2	10A4	10A6	10A8	10A10	Units
Maximum repetitive peak reverse voltage	V <sub>RRM</sub>	50	100	200	400	600	800	1000	Volts
Maximum RMS voltage	V <sub>RMS</sub>	35	70	140	280	420	560	700	Volts
Maximum DC blocking voltage	V <sub>DC</sub>	50	100	200	400	600	800	1000	Volts
Maximum average forward rectified current @T <sub>A</sub> =50 °C	I <sub>F(AV)</sub>	10						Amps	
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC method)	I <sub>FSM</sub>	600						Amps	
Maximum forward voltage at 10A DC	V <sub>F</sub>	1						Volts	
Maximum DC reverse current @T <sub>J</sub> = 25 °C at rated DC blocking voltage @T <sub>J</sub> = 100 °C	I <sub>R</sub>	10 100						µA	
Typical junction capacitance (Note 1)	C <sub>J</sub>	150						pF	
Typical thermal resistance (Note 2)	R <sub>θJA</sub>	10						°C/W	
Operating temperature range	T <sub>J</sub>	-55 to+125						°C	
Storage temperature range	T <sub>S</sub>	-55 to+150						°C	

Notes: 1. Measured at 1 MHz and applied reverse voltage of 4V D.C.

2. Thermal Resistance Junction to Ambient.

